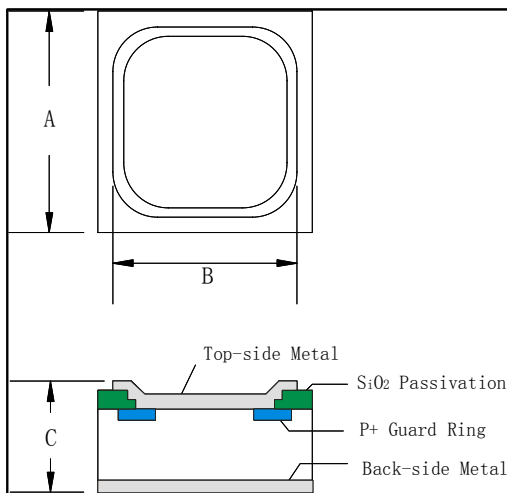


<b>SCHOTTKY DIE SPECIFICATION</b>	TYPE: SB160
General Description: 60 V 1 A ( <input checked="" type="checkbox"/> Standard <input type="checkbox"/> Low) VF ,	( <input checked="" type="checkbox"/> Single <input type="checkbox"/> Dual) Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	60		Volt
Average Rectified Forward Current	IFAV	1		Amp
Maximum Instantaneous Forward Voltage				
@ 1 Ampere, Ta=25°C	VF MAX	0.630		Volt
Reverse current				
@ VR= 63 Volt, Ta=25°C	IR MAX	0.100		mA
<b>MAXIMUM RATINGS</b>				
Nonrepetitive Peak Surge Current	IFSM	32		Amp
Operating Junction Temperature	Tj	125		°C
Storage Temperature	TSTG	-50 to +150		°C

Specifications apply to die only. Actual performance may degrade when assembled.  
 We do not guarantee device performance after assembly.  
 Data sheet information is subjected to change without notice.

**DICE OUTLINE DRAWING**



DIM	ITEM	μ m	Mil
A	Die Size	838	32.99
B	Top Metal Pad Size	750	29.52
C	Thickness (Min)	280	11.00
	Thickness (Max)	300	11.80

**PS:**

- (1)Cutting street width is around 16 μ m (0.62mil).
- (2)Both of top-side and back-side metals are Ti/Ni/Ag.